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Siliup Semiconductor

BSS84KT7

60V P-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	4.2Ω@-10V	-0.13A
	4.5Ω@-4.5V	

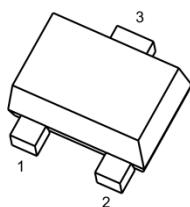
Feature

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- ESD Protected

Application

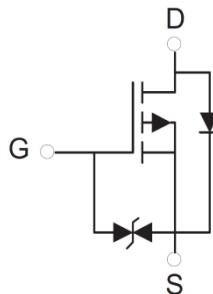
- DC-DC converters
- load switching
- power management in portable
- battery-powered products

Package

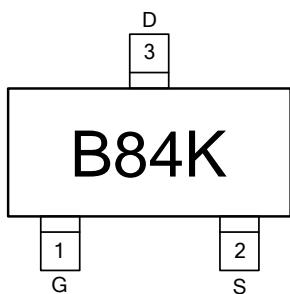


SOT-723

Circuit diagram



Marking



B84K =Device Code



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Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	-0.13	A
Plused Drain Current @ t _p <10μs	I _{DM}	-0.52	A
Power Dissipation	P _D	0.2	W
Thermal Resistance from Junction to Ambient ⁽²⁾	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-60	-	-	V
Drain Leakage Current	I _{DSS}	V _{DS} =-48V, V _{GS} = 0V	-	-	-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V	-	-	±10	μA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.8	-1.5	-2.5	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} =-10V, I _D =-0.15A	-	4.2	6	Ω
		V _{GS} =-4.5V, I _D =-0.15A	-	4.5	7	
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =-5V, V _{GS} =0V, f =1MHz	-	30	-	pF
Output Capacitance	C _{oss}		-	10	-	
Reverse Transfer Capacitance	C _{rss}		-	5	-	
Switching characteristics⁽⁴⁾						
Turn-on delay time	t _{d(on)}	V _{DD} =-15V, R _L =50Ω, I _D =-2.5A	-	2.5	-	ns
Turn-on rise time	t _r		-	1	-	
Turn-off delay time	t _{d(off)}		-	16	-	
Turn-off fall time	t _f		-	8	-	
Source-Drain Diode characteristics						
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =-0.5A	-	-	-1.3	V

Notes:

1. Repetitive rating: Pulse width limited by junction temperature.
2. Surface mounted on FR4 board, t≤10s.
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.
4. Guaranteed by design, not subject to production.



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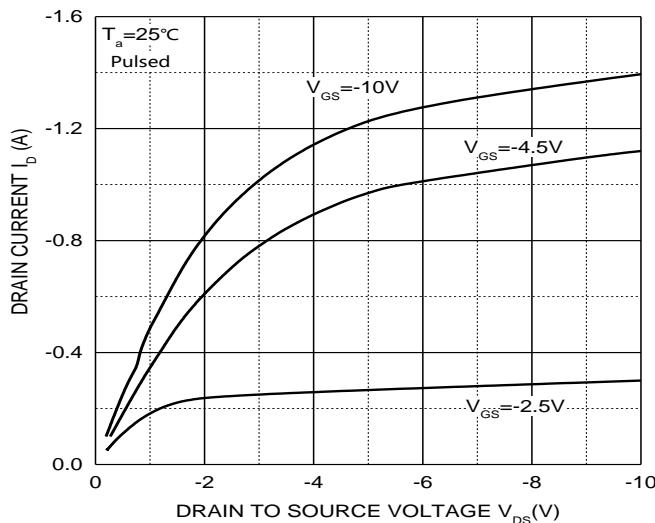
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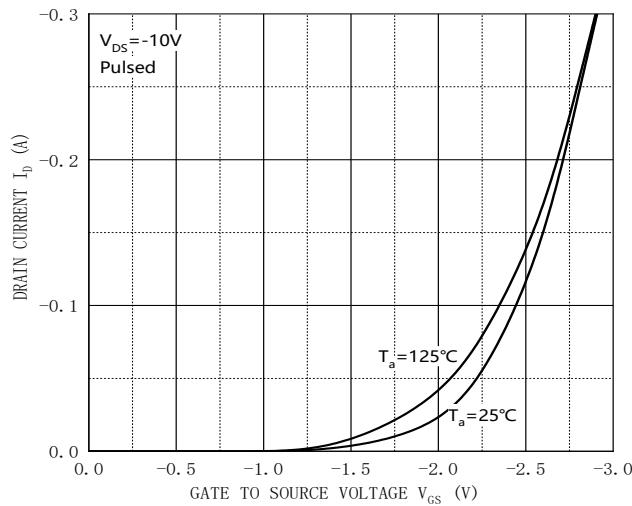
60V P-Channel MOSFET

Typical Characteristics

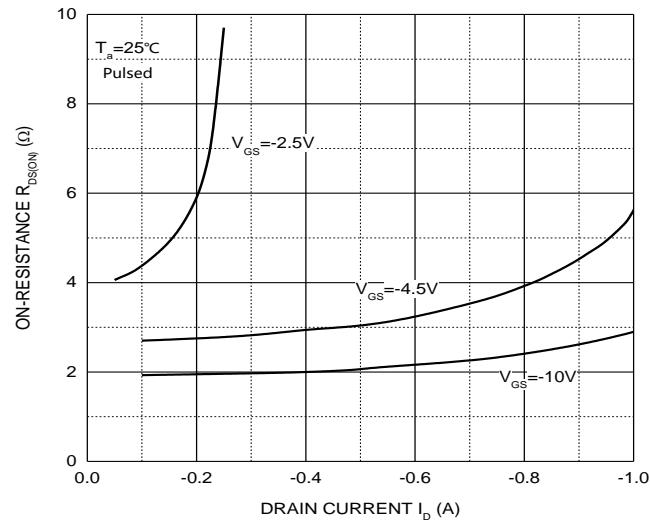
Output Characteristics



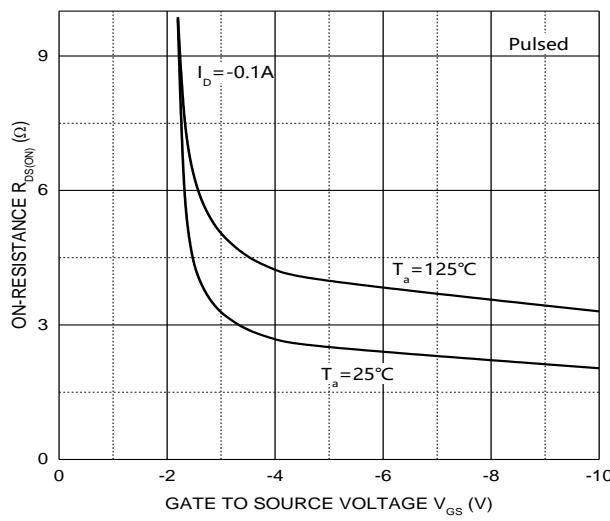
Transfer Characteristics



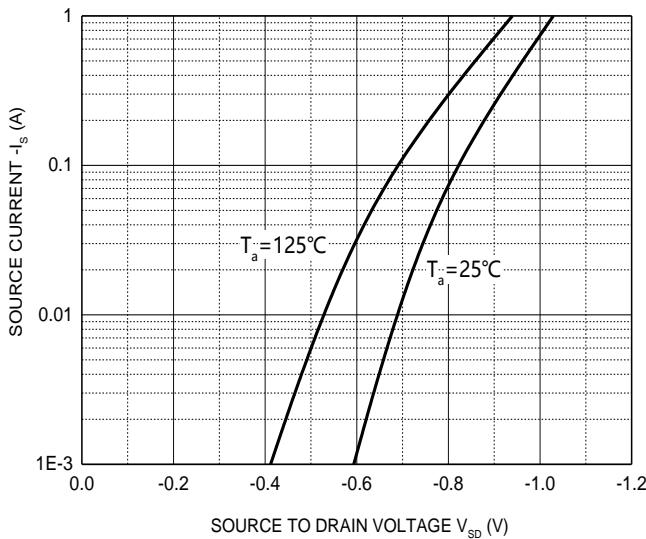
$R_{DS(ON)}$ vs. I_D



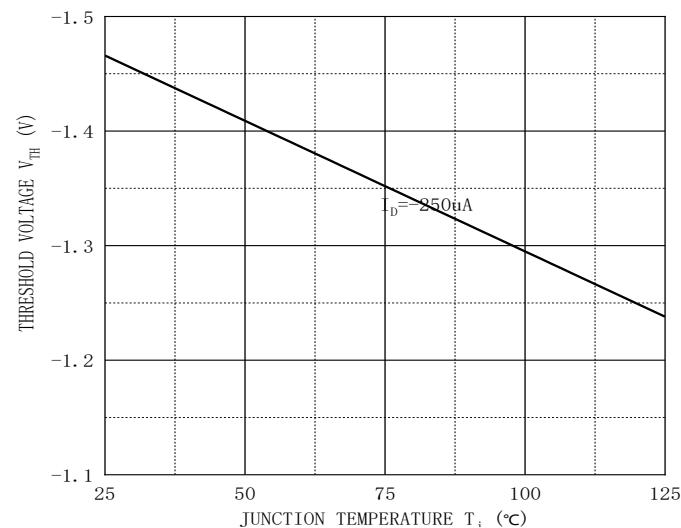
$R_{DS(ON)}$ vs. V_{GS}



I_S vs. V_{SD}



Threshold Voltage





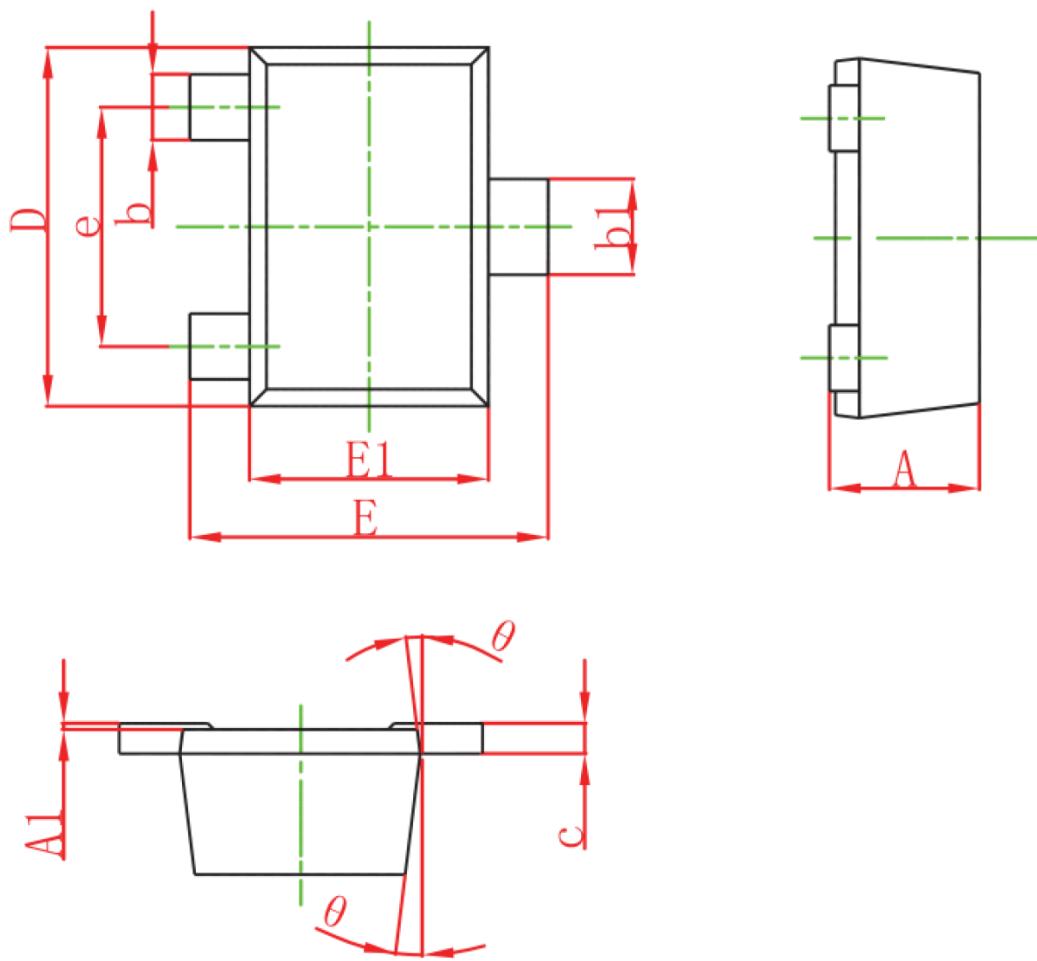
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SOT-723 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.430	0.500
A1	0.000	0.050
b	0.170	0.270
b1	0.270	0.370
C	0.080	0.150
D	1.150	1.250
E	1.150	1.250
E1	0.750	0.850
e	0.800 Typ.	
θ	7°Ref.	